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SEP 16 2005

SCULLY, SCOTT, MURPHY

400 Garden City Plaza – Suite 300 Garden City, New York 11530 (516) 742-4343 - Telephone (516) 742-4366 – Facsimile e-mail: intprop@ssmp.com



To: Examiner Fernando L. Toledo From: Leslie S. Szivos

Art Unit: 2823

Fax: 571-273-8300 Pages: 6 pages including fax cover

Phone: Date: 9/16/2005

Phone: Date: 9/10/2005

Hussein I. Hanafi et al.

Re: U.S. Patent Appln. No. 10/659,949 CC:

Docket: YOR920020182US2 (15790A)

URGENT!!

Please see the following documents:

- Certificate of transmission by facsimile dated September 16, 2005
- 2. Transmittal letter (in duplicate)
- 3. Authorization to charge IBM deposit account
- 4. Response under 37 C.F.R. §§1.111 and 1.143

If you have any questions concerning this facsimile please do not hesitate to contact Vivian Henriquez at 516-742-4343. Thank you.

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| CERTIFICATE OF Applicant(s): Hussein I. | Docket No. YOR920020182US2 (15790A) | | | | | | | |
|--|--|--------------------------------|--|------------------------|--|--|--|--|
| Application No. 10/659,949 | Filing Date September 11, 2003 | Examiner Fernando L. Toledo | | Group Art Unit 2823 | | | | |
| Invention: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETCH | | | | | | | | |
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| I hereby certify that this Response under 37 C.F.R. §§1.111 AND 1.143 (Identify type of correspondence) is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. 571-273-8300 | | | | | | | | |
| on September 11, 2005 (Date) | | | | | | | | |
| Leslie S. Szwos, Ph.D. (Typed or Printed Napre of Period Signing Certificate) (Signature) | | | | | | | | |
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| | Docket No. YOR920020182US2 (15790A) | | | | | | | |
|---|--|--------------------------------|--|------------------------|--|--|--|--|
| In Re Application Of: Hussein I. Hanafi et al. | | | | | | | | |
| Application No. 10/659,949 | Filing Date September 11, 2003 | Examiner Fernando L. Toledo | Customer No. 23389 | Group Art Unit 2823 | Confirmation No. 5877 | | | |
| Title: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETHCH | | | | | | | | |
| | • | COMMISSIONER FOR PAT | ENTS: | | | | | |
| Transmitted herew | rith is: | | | | | | | |
| Response under | 37 C.F.R. §§1.111 and | 1 1.143 | | · | | | | |
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| in the above identified application. No additional fee is required. A check in the amount of is attached. The Director is hereby authorized to charge and credit Deposit Account No. 50-0510/IBM as described below. Charge the amount of Credit any overpayment. Charge any additional fee required. Payment by credit card. Form PTO-2038 is attached. WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038. | | | | | | | | |
| - ! | 1/8/ | | Dated: Sept | ember 16, 2005 | | | | |
| Leslie S. Szivos, Ph Reg. No. 39,394 | Sighature | | | | | | | |
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| | | | addressed to the 1450, Alexandria (Date) | , VA 29313-1450" [| for Patritis, P.O. Box 37 FR 1.8(a)] on | | | |
| LSS:vh | | · | Signatur | e Person Mailing | Correspondence | | | |
| cc: | | | Type or Printe | d Name of Person M | ailing Correspondence | | | |
| | | | | | P164/9FV03 | | | |

| | TRANSMIT (General - P | Docket No. YOR920020182US2 (15790A) | | | | | | |
|---|--------------------------------|--|--|---|---|--|--|--|
| In Re Application Of: Hussein I. Hanafi et al. | | | | | | | | |
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| | | COMMISSIONER FOR PAT | ENTS: | | | | | |
| Transmitted herewith is: Response under 37 C.F.R. §§1.111 and 1.143 | | | | | | | | |
| in the above identified application. No additional fee is required. A check in the amount of is attached. The Director is hereby authorized to charge and credit Deposit Account No. 50-0510/IBM as described below. Charge the amount of Credit any overpayment. Charge any additional fee required. Payment by credit card. Form PTO-2038 is attached. WARNING: Information on this form may become public. Credit card Information should not be included on this form. Provide credit card information and authorization on PTO-2038. | | | | | | | | |
| Leslie S. Szivos, Pl Reg. No. 39,394 | | | Dated: Sept | ember 16, 2005 | | | | |
| 400 Garden City P Garen City, New Y LSS:vh | | SER | sufficient pesta addressed to the 1450, Alexandria (Date) | n the United State ge as first class n "Commissioner a, VA 22313-1450" | s Postal Service with mail in envelope for Patents, P.O. Box 32 CFR 1.8(a)] on | | | |
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Hussein I. Hanafi et al.

Examiner: Fernando L. Toledo

Serial No: 10/659,949

Art Unit: 2823

Filed: September 11, 2003

Docket: YOR920020182US2 (15790A)

For: LOW RESISTANCE T-GATE MOSFET

Dated: September 16, 2005

DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE

REMOVAL ETCH

Confirmation No.: 5877

Mail Stop Amendment Commissioner for Patents United States Patent Office Alexandria, VA 23313-1450

RESPONSE UNDER 37 C.F.R. §§1.111 AND 1.143

Sir:

In response to the Office Action dated August 16, 2005, applicants provisionally elect, without traverse, the subject matter of Group II, i.e., Claims 14-20 for continued prosecution in the above-identified patent application.

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that this paper is being facsimile transmitted to the Patent and Trademark Office on the date shown below.

Dated: September 16, 2005

Leslie S. Szivos